

# C.U.SHAH UNIVERSITY

## Summer Examination-2018

Subject Name: CMOS VLSI Design

Subject Code: 5TE01CVD1

Branch: M.Tech (VESD)

Semester: 1

Date: 19/03/2018

Time: 02:30 To 05:30

Marks: 70

### Instructions:

- (1) Use of Programmable calculator and any other electronic instrument is prohibited.
  - (2) Instructions written on main answer book are strictly to be obeyed.
  - (3) Draw neat diagrams and figures (if necessary) at right places.
  - (4) Assume suitable data if needed.
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### SECTION – I

- Q-1**            **Define the following terms** **(07)**
- a. Noise Margin
  - b. Transistor sizing.
  - c. Threshold Voltage.
  - d. Transmission Gate
  - e. Body effect
  - f. Static Power Consumption.
  - g. Power Delay Product.

- Q-2**            **Attempt all questions** **(14)**
- (a) Explain the minimization of RC effect in CMOS inverter chain.
  - (b) Explain the characteristic and operation of NMOS Enhancement transistor.

**OR**

- Q-2**            **Attempt all questions** **(14)**
- (a) Derive the CMOS inverter DC characteristics and obtain the relationship for output voltage at different region in the transfer characteristics.
  - (b) Explain with neat diagrams the Multiplexer and latches using Transmission Gate.

- Q-3**            **Attempt all questions** **(14)**
- (a) Derive the equation of fall time for CMOS inverter.
  - (b) Design a circuit and layout diagram for two input CMOS NAND and NOR gate.

**OR**

- Q-3**            **Attempt all questions** **(14)**
- (a) Derive the capacitances of three regions of operation of MOS device.
  - (b) Explain the fringing effects in MOS device.



## SECTION – II

- Q-4**      **Define the following terms**      (07)
- a. Tri-state logic
  - b. Bi-directional Pads
  - c. Dynamic MOS RAM Cell
  - d. Routing capacitance of MOS
  - e. Synchronous Counter
  - f. Latch
  - g. Ripple Carry

- Q-5**      **Attempt all questions**      (14)
- (a) Explain Pseudo 2-phase memory structures.
  - (b) Write note on Clocked CMOS logic.

**OR**

- Q-5**      **Attempt all questions**      (14)
- (a) Draw and explain Pseudo nMOS logic in detail.
  - (b) Explain Pseudo 4-phase clocking

- Q-6**      **Attempt all questions**      (14)
- (a) Explain with diagram the IDDQ testing.
  - (b) Explain the design of Dynamic Combinational Adder.

**OR**

- Q-6**      **Attempt all Questions**      (14)
- (a) Explain the design of Booth multiplier circuit.
  - (b) Explain the parallel multiplier based on partial product generation.

